

## 30V N-Channel MOSFET

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
30V	3Ω@10V	100mA
	4Ω@4.5V	

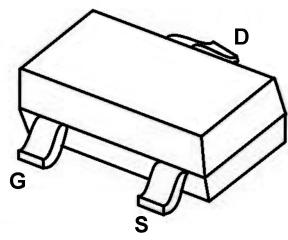
### Feature

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Easily designed drive circuits
- Easy to parallel

### Application

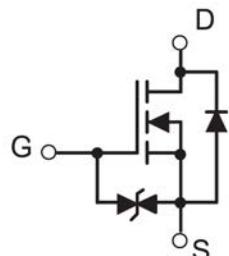
- Interfacing , Switching

### Package



SOT-323

### Circuit diagram



**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	100	mA
Power Dissipation	P <sub>D</sub>	0.2	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

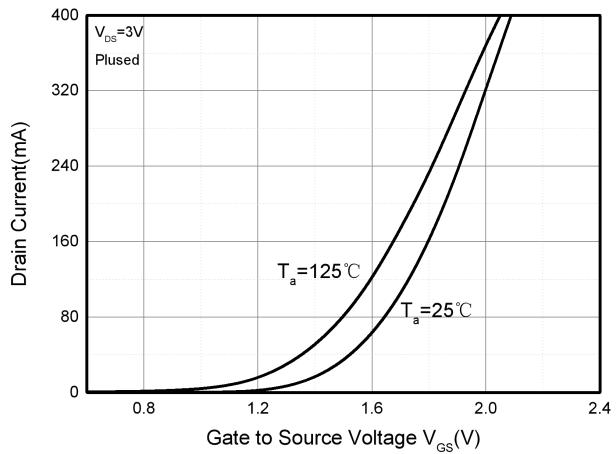
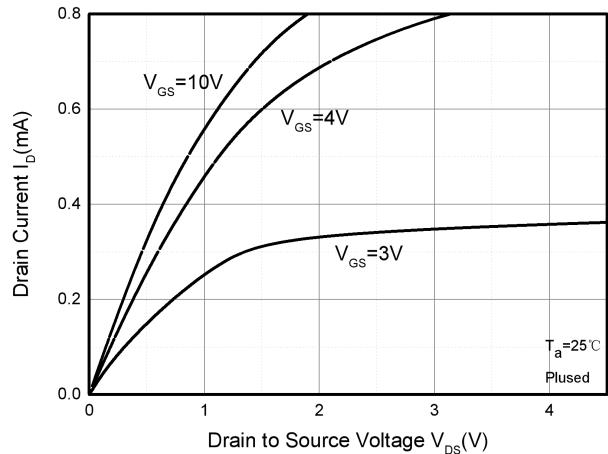
**Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)**

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±5	μA
Gate threshold voltage <sup>1)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.8	1	1.45	V
Drain-source on-resistance <sup>1)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 500mA		1.5	3	Ω
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA		1.8	4	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz		27		pF
Output Capacitance	C <sub>oss</sub>			13		
Reverse Transfer Capacitance	C <sub>rss</sub>			6		
<b>Switching Characteristics<sup>1)2)</sup></b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =0.29A, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω			5	nS
Rise time	tr				18	
Turn-off delay time	t <sub>d(off)</sub>				36	
Fall time	tf				14	
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 500mA	0.5		1.4	V

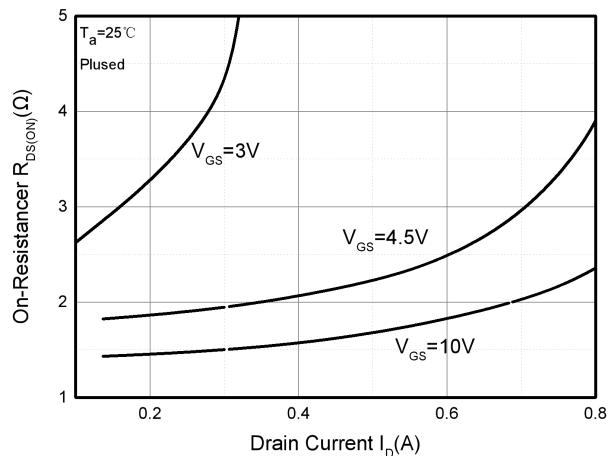
**Notes:**

- 1) Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%.
- 2) These parameters have no way to verify.

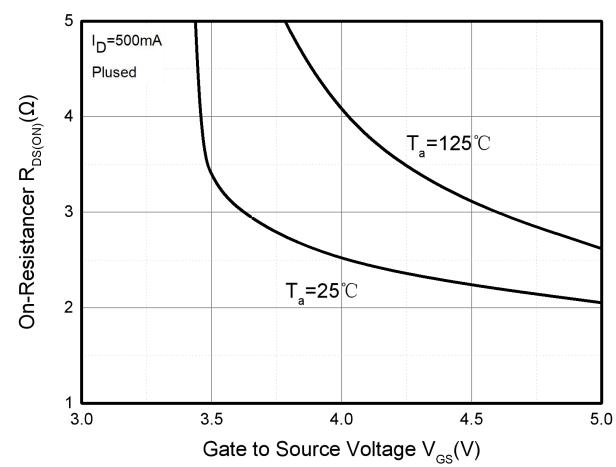
## Typical Characteristics



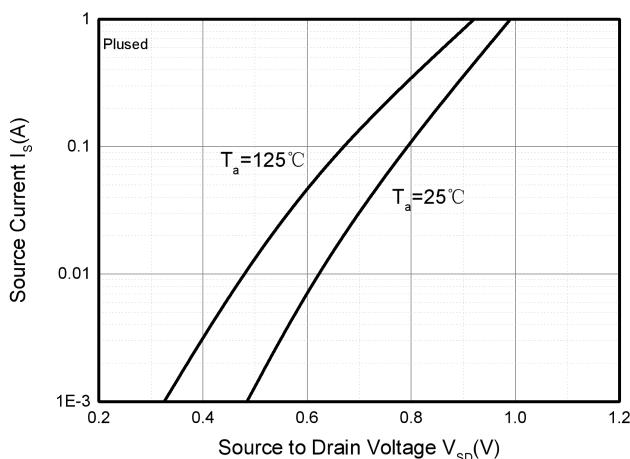
## Output Characteristics



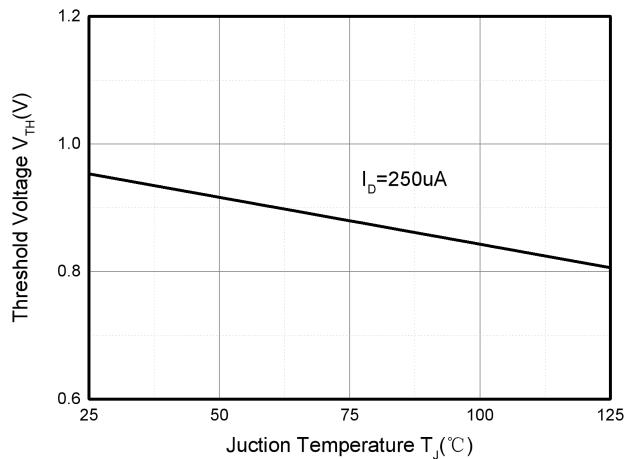
RDS(ON) — ID



RDS(ON) — VGS

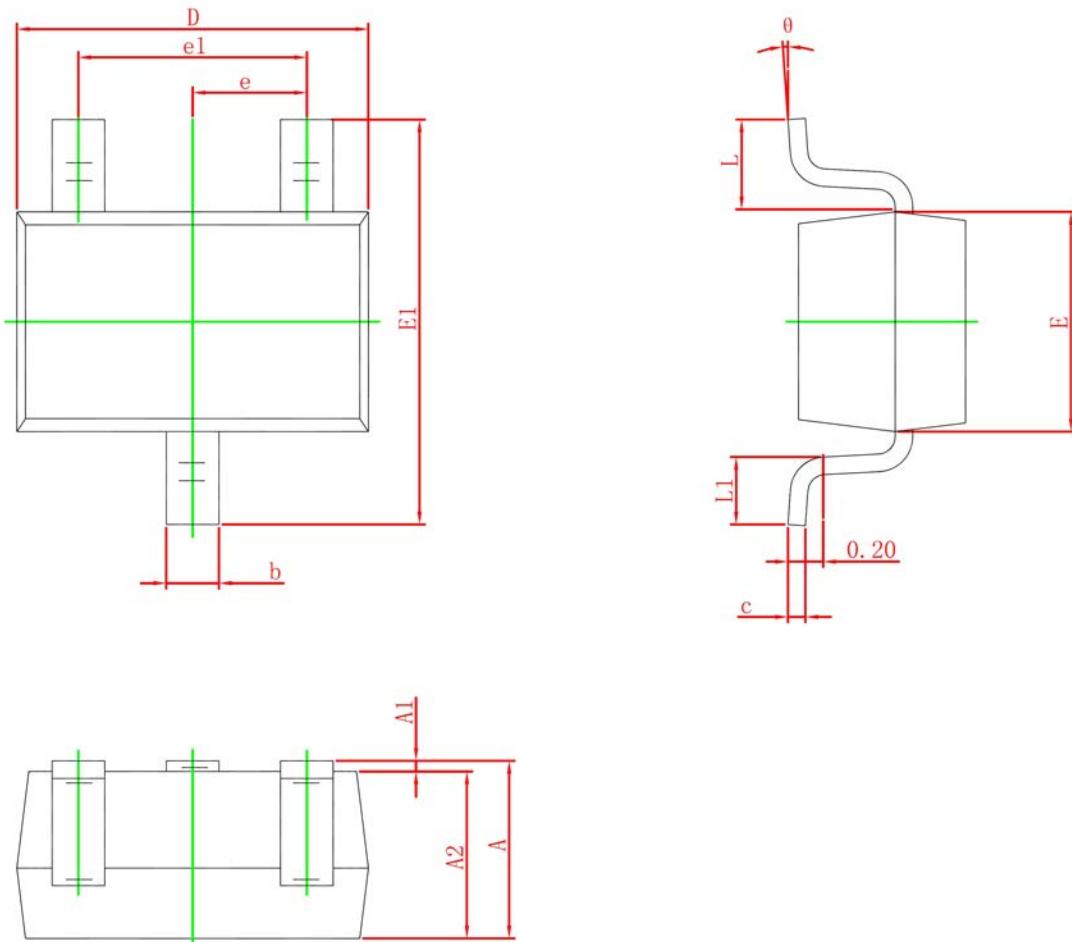


IS — VSD



Threshold Voltage

## SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

V 1.0